

L Number	Hits	Search Text	DB	Time stamp
1	50	("438/908").CCLS.	USPAT	2001/03/16 14:40
2	396425	barrier and arc and etch stop	USPAT	2001/03/16 14:43
3	42	"in situ"	USPAT	2001/03/16 14:41
4	13236	"in-situ"	USPAT	2001/03/16 14:41
5	13263	"in situ" or "in-situ"	USPAT	2001/03/16 14:41
6	1526	"in-situ" and (barrier and arc and etch stop)	USPAT	2001/03/16 14:42
7	38830	438/\$.ccls.	USPAT	2001/03/16 14:43
8	444	("in-situ" and (barrier and arc and etch stop)) and 438/\$.ccls.	USPAT	2001/03/16 14:43
9	3	barrier with arc with "etch stop"	USPAT	2001/03/16 14:43
10	0	"in-situ" with (barrier with arc with "etch stop")	USPAT	2001/03/16 14:43
11	0	"in-situ" same (barrier with arc with "etch stop")	USPAT	2001/03/16 14:44
12	149	("in situ" or "in-situ") with (barrier or arc or "etch-stop")	USPAT	2001/03/16 14:44
13	28	((("in situ" or "in-situ") with (barrier or arc or "etch-stop"))) and (barrier and arc and etch stop)	USPAT	2001/03/16 14:44
14	34226	sic or "silicon carbide"	USPAT	2001/03/16 14:51
16	2979	organosilane	USPAT	2001/03/16 14:51
17	2	((("in situ" or "in-situ") with (sic or "silicon carbide"))) and organosilane	USPAT	2001/03/16 14:51
15	41	("in situ" or "in-situ") with (sic or "silicon carbide")	USPAT	2001/03/16 14:55
18	1089	moslehi	USPAT	2001/03/16 14:55
19	483	438/\$.ccls. and moslehi	USPAT	2001/03/16 14:56
20	1021754	apparatus	USPAT	2001/03/16 14:56
21	165	(438/\$.ccls. and moslehi) and apparatus	USPAT	2001/03/16 16:47
22	1389	5.ab.	USPAT	2001/03/16 16:47
23	169	5.ab. and 438/\$.ccls.	USPAT	2001/03/16 16:48
24	5	(5.ab. and 438/\$.ccls.) and (sic or "silicon carbide")	USPAT	2001/03/16 16:48

	L #	Hits	Search Text	DBs
1	L1	74530	427/\$.ccls.	USPAT
2	L2	271087	sic or silicon carbide	USPAT
3	L3	97842	plasma	USPAT
4	L4	129644	argon or helium or noble	USPAT
5	L5	2520	1 and 2 and 3 and 4	USPAT
6	L6	624	methysilane	USPAT
7	L7	47	5 and 6	USPAT

	L #	Hits	Search Text	DBs
1	L2	32251	sic or "silicon carbide"	USPAT
2	L3	4938	silane with silicon and carbon	USPAT
3	L4	869	silane with silicon with carbon	USPAT
4	L5	224	2 and 4	USPAT
5	L6	112	2 same 4	USPAT
6	L7	78	2 with 4	USPAT
7	L8	6993	silicon with carbon with 2	USPAT
8	L9	71418	438/\$.ccls. or 257/\$.ccls.	USPAT
9	L10	423	9 and 8	USPAT
10	L12	624	methysilane	USPAT
11	L13	10	11 and 12	USPAT
12	L11	408	10 not 7	USPAT
13	L14	857316	source or precursor	USPAT
14	L15	4	8 with 12	USPAT
15	L16	384	8 with 14	USPAT
16	L17	31	16 and 11	USPAT
17	L18	10	11 and 12	USPAT
18	L19	97842	plasma	USPAT
19	L20	228	19 and 11	USPAT
20	L21	171	14 and 20	USPAT

	Hits	Search Text	DBs
1	52805	(SIC OR "SILICON CARBIDE")	EPO; JPO; Derwent
2	433	(METHYLSILANE OR ALKYLSILANE)	EPO; JPO; Derwent
3	19	((METHYLSILANE OR ALKYLSILANE)) AND ((SIC OR "SILICON CARBIDE"))	EPO; JPO; Derwent
4	493	("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")	EPO; JPO; Derwent
5	4	((("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")) WITH ((SIC OR "SILICON CARBIDE")))	EPO; JPO; Derwent
6	0	((("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")) WITH ((SIC OR "SILICON CARBIDE")))	USPAT
7	0	((("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER"))	USPAT
8	493	("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")	EPO; JPO; Derwent
9	1575	("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")	USPAT
10	0	((("INTERLEVEL DIELECTRIC" OR "ANTI-REFLECTIVE LAYER")) with ((SIC OR "SILICON CARBIDE"))	USPAT